



SOT-23 Plastic-Encapsulate Transistors

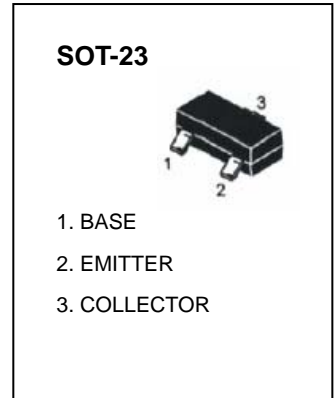
2SC1815

C1815 TRANSISTOR (NPN)

FEATURES

Power dissipation

MARKING : C1815=HF



MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	200	mW
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=40\text{V}, I_B=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.30	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=1\text{mA}, f=30\text{MHz}$	80			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	200-300	300-400